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Information Disclosure Statement By Applicant

# Information Disclosure Statement By Applicant

Substitute for form 1449/PTO

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Application Number: 10/828,356

Filing Date: 04/19/2004

First Named Inventor: King

Art Unit: 2811

Examiner Name: N/A

Attorney Docket Number: PRG2001-5CD3

Examiner Initials	Patent Number	Publication Date	Inventor Name
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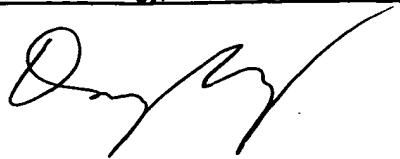
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Attorney Docket Number: PRG2001-5CD3

Examiner Initials	Other Publications
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DM	News Release from <a href="http://www.eurekalert.org/releases/udel-udcnfib.html">www.eurekalert.org/releases/udel-udcnfib.html</a> , " UD Computer News: Future Looks Bright for Tunnel Diodes, Promising Faster, More Efficient Circuits," October 1, 1998, 4 pages.
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DM	JIAN FU ZHANG, "Traps," Wiley Encyclopedia of Electrical and Electronics Engineering Online, Article Posting Date: December 27, 1999, John Wiley & Sons, Inc., 2 Pages.
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